2SB1261L

Rev.E Mar.-2016

蓝箭电子 BLUE ROCKET ELECTRONICS

DATA SHEET

/ Descriptions

TO-126F PNP Silicon PNP transistor in a TO-126F Plastic Package.

/ Features

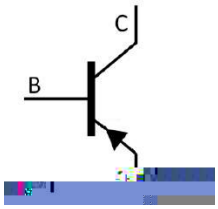
h_{FE}

Excellent h_{FE} linearity, low $V_{CE(sat)}$, high P_C.

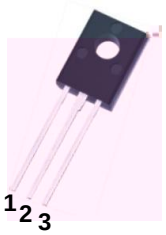
/ Applications

Audio frequency amplifier and switching, especially in hybrid integrated circuits applications.

/ Equivalent Circuit



/ Pinning



PIN1 Emitter PIN 2 Collector PIN 3 Base

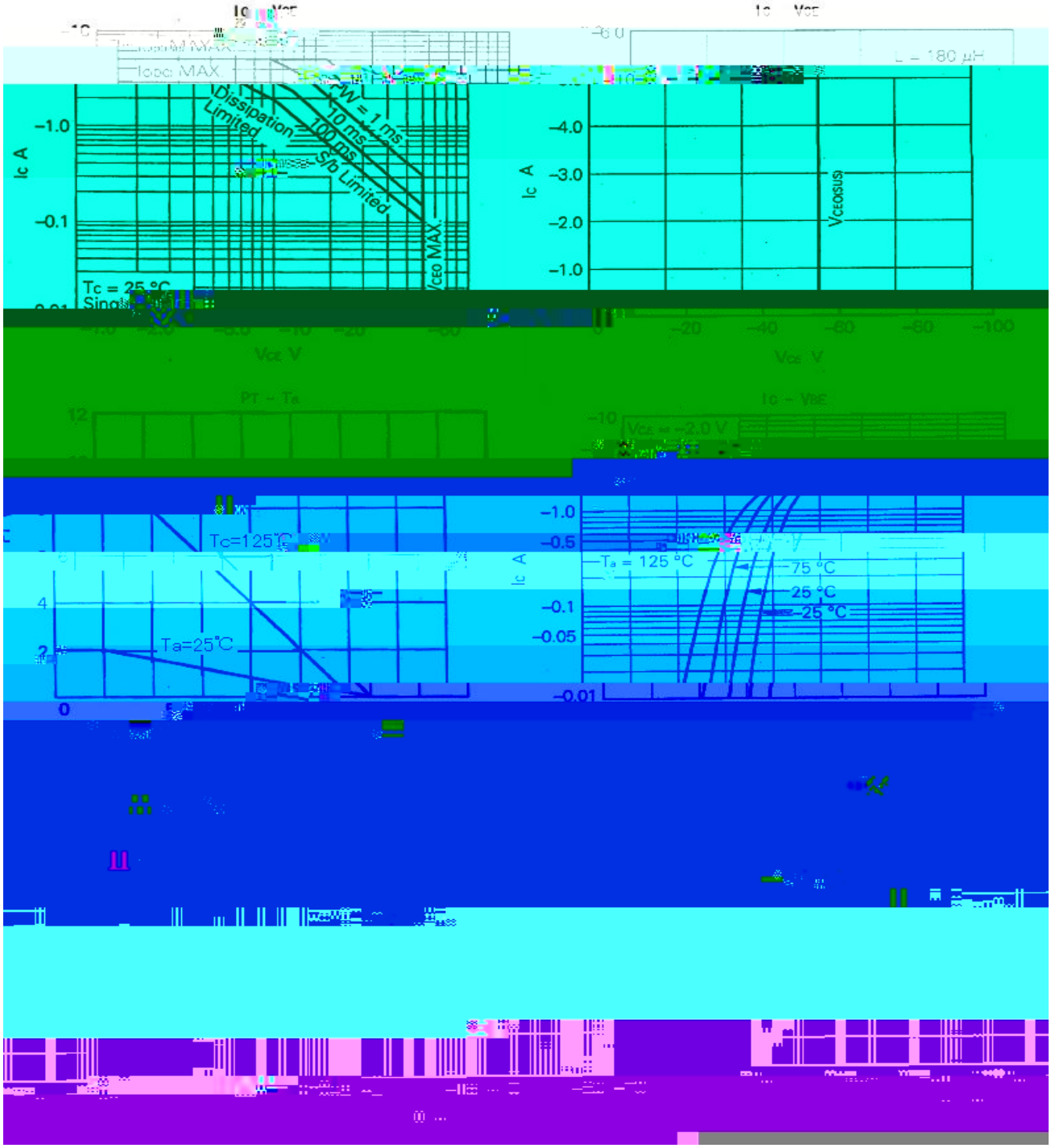
/ h_{FE} Classifications & Marking

h_{FE} Classifications Symbol	M	L	K
h_{FE} Range	100 200	160 320	200 400

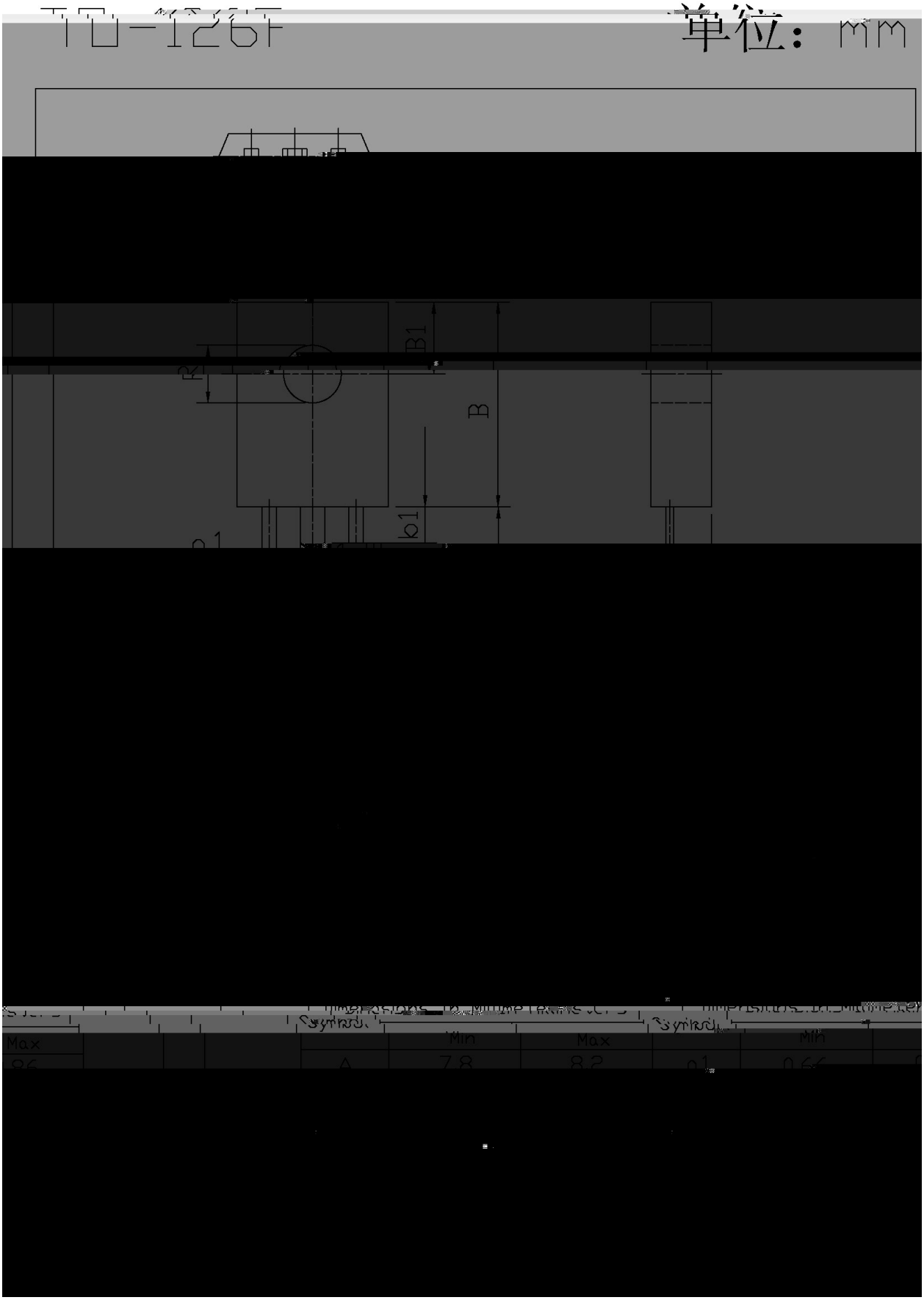
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-60	V
Collector to Emitter Voltage	V_{CEO}	-60	V
Emitter to Base Voltage	V_{EBO}	-7.0	V
Collector Current - Continuous	I_C	-3.0	A
Collector Power Dissipation	P_C	2.0	W
Collector Power Dissipation	P_C(Tc=125)	10	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=-0.1mA I_E=0	-60			V
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=-1.0mA I_B=0	-60			V
Emitter to Base Breakdown Voltage	V_{EBO}	I_E=-0.1mA I_C=0	-7.0			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=-60V I_E=0			-10	μA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=-7.0V I_C=0			-10	μA
DC Current Gain	$h_{FE(1)}$	V_{CE}=-2.0V I_C=-600mA	100		400	
	$h_{FE(2)}$	V_{CE}=-2.0V I_C=-200mA	60			
	$h_{FE(3)}$	V_{CE}=-2.0V I_C=-2.0A	50			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=-1.5A I_B=-150mA			-0.3	V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	I_C=-1.5A I_B=-150mA			-1.2	V
Transition Frequency	f_T	V_{CE}=-5.0V I_C=-1.5A		50		MHz
Collector Output Capacitance	C_{ob}	V_{CB}=-10V I_E=0 f=1.0MHz		40		pF

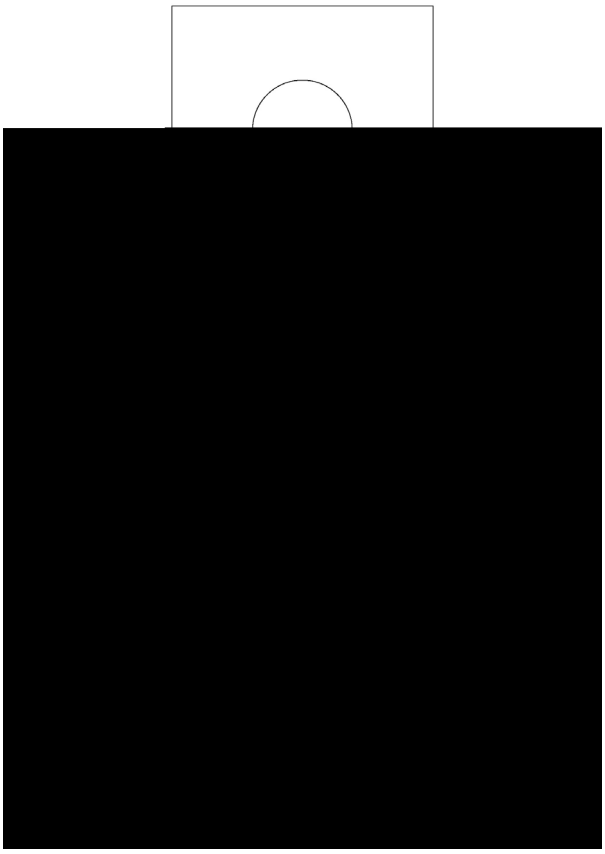
/ Electrical Characteristic Curve



/ Package Dimensions



/ Marking Instructions



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M: h_{FE}

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